2SC3935

Silicon NPN epitaxial planar type

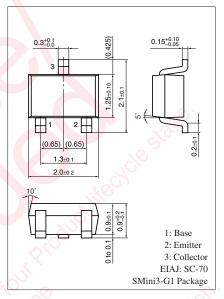
For high-frequency amplification/oscillation/mixing

■ Features

- High transition frequency f_T
- Small collector output capacitance (Common base, input open circuited) C_{ob} and reverse transfer capacitance (Common base) C_{rb}
- S-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing

■ Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V _{CBO}	15	V	
Collector-emitter voltage (Base open)	V _{CEO}	10	V	
Emitter-base voltage (Collector open)	V _{EBO}	3	V	
Collector current	I_{C}	50	mA	
Collector power dissipation	P_{C}	150	mW	
Junction temperature	T _j	150	°C	
Storage temperature	T _{stg}	-55 to +150	°C	



Marking Symbol: 1S

■ Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V _{CEO}	$I_C = 2 \text{ mA}, I_B = 0$	10		ن. ان	V
Emitter-base voltage (Collector open)	V _{EBO}	$I_E = 10 \mu\text{A}, I_C = 0$	3	60/		V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 10 \text{ V}, I_{E} = 0$	D. C.	0.	1	μΑ
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CE} = 10 \text{ V}, I_{B} = 0$	00,		10	μΑ
Forward current transfer ratio	h _{FE1} *1	$V_{CE} = 2.4 \text{ V}, I_{C} = 7.2 \text{ mA}$	75		220	_
	h _{FE2}	$V_{CE} = 2.4 \text{ V}, I_{C} = 100 \mu\text{A}$	75			
h _{FE} ratio	Δh_{FE}^{*2}	h_{FE2} : $V_{CE} = 2.4 \text{ V}$, $I_{C} = 100 \mu A$	0.75		1.60	_
		$h_{\text{FE}1}$: $V_{\text{CE}} = 2.4 \text{ V}$, $I_{\text{C}} = 7.2 \text{ mA}$				
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = 20 \text{ mA}, I_B = 4 \text{ mA}$			0.5	V
Transition frequency	f_T	$V_{CB} = 4 \text{ V}, I_E = -7.2 \text{ mA}, f = 200 \text{ MHz}$	1.4	1.9	2.5	GHz
Collector output capacitance	C _{ob}	$V_{CB} = 4 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		0.9	1.1	pF
(Common base, input open circuited)						
Reverse transfer capacitance	C _{rb}	$V_{CB} = 4 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$		0.25	0.35	pF
(Common base)						
Collector-base parameter	r _{bb} ' • C _C	$V_{CB} = 4 \text{ V}, I_E = -5 \text{ mA}, f = 31.9 \text{ MHz}$		11.8	13.5	ps

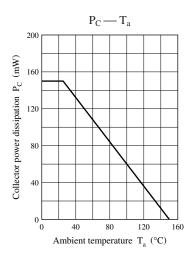
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

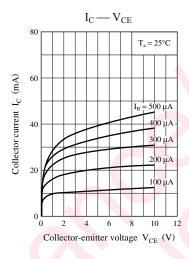
2. *1: Rank classification

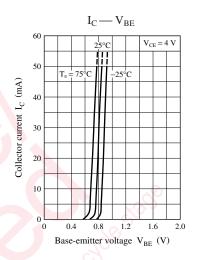
Rank	Р	Q		
h _{FE}	75 to 130	110 to 220		

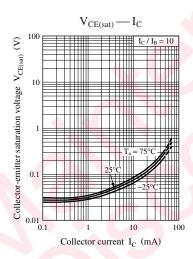
^{*2:} $\Delta h_{FE} = h_{FE2}$ / h_{FE1}

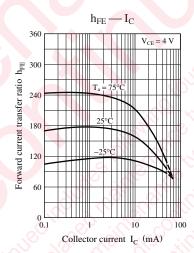
Panasonic

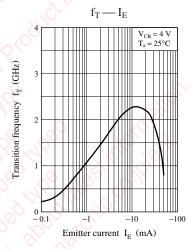


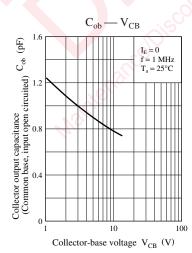












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